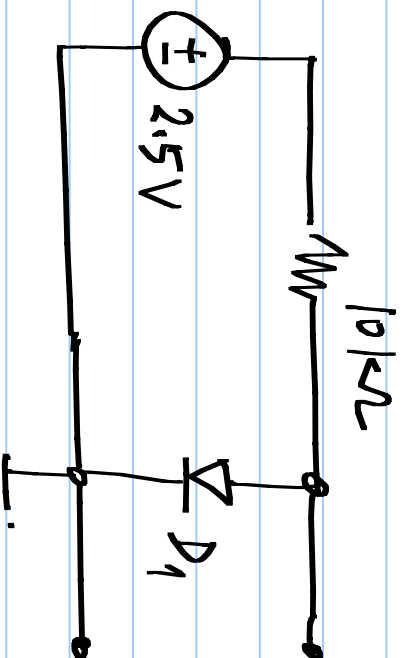


# Using SPICE-like simulators for circuit analysis

Example circuit:

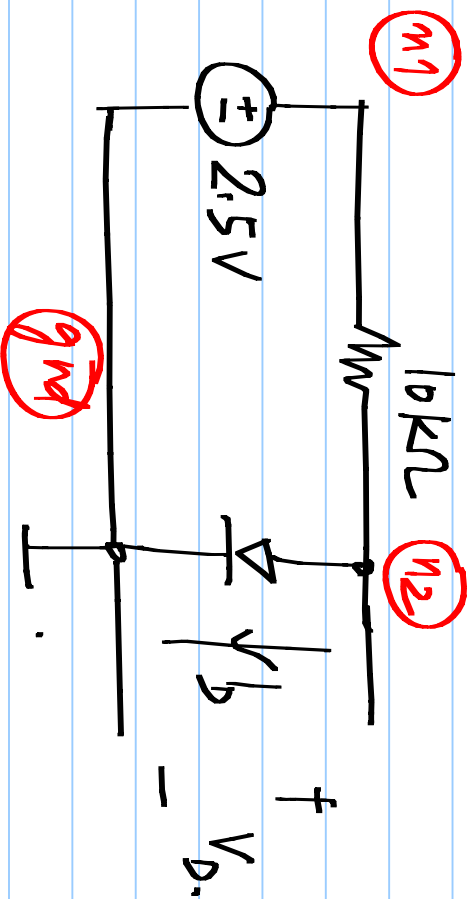


D<sub>1</sub>: "ideal-diode"

Analysis that one would  
like to do:

- \* Operating point (DC)
- \* Small signal incremental analysis (AC)
- \* Analysis with large time varying signals (transient)

## DC operating point analysis:



\* Do .op analysis & determine  $V_D$ ,  $I_D$

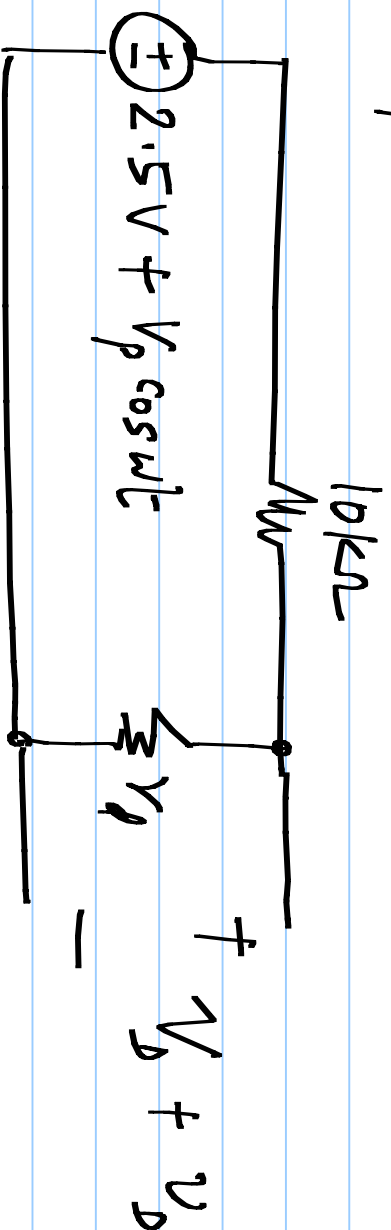
Small signal incremental analysis :

(Hand calculation)

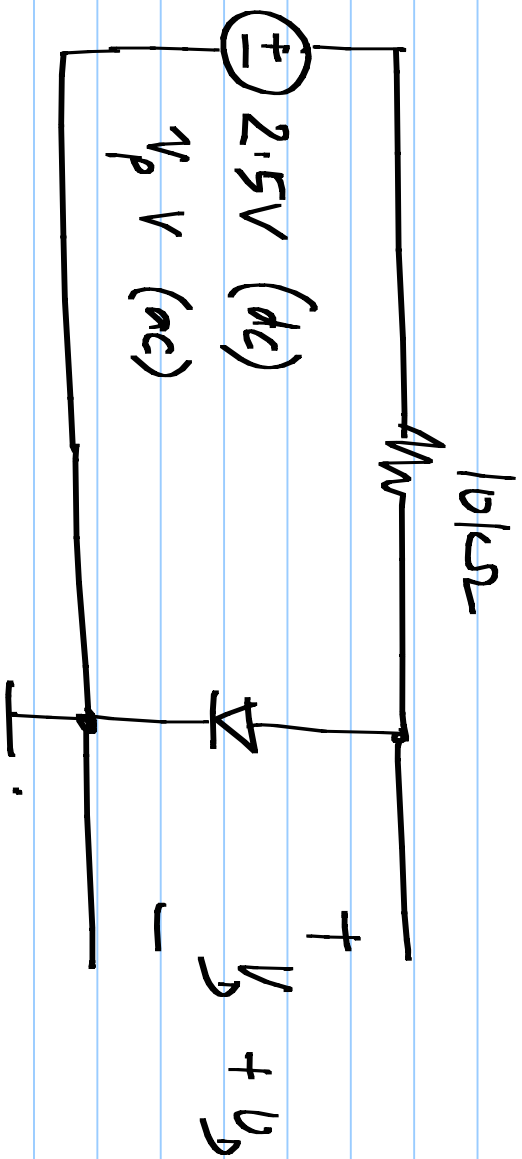
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\* Determine the small signal equivalent of the diode .

\* Analyze the circuit below .



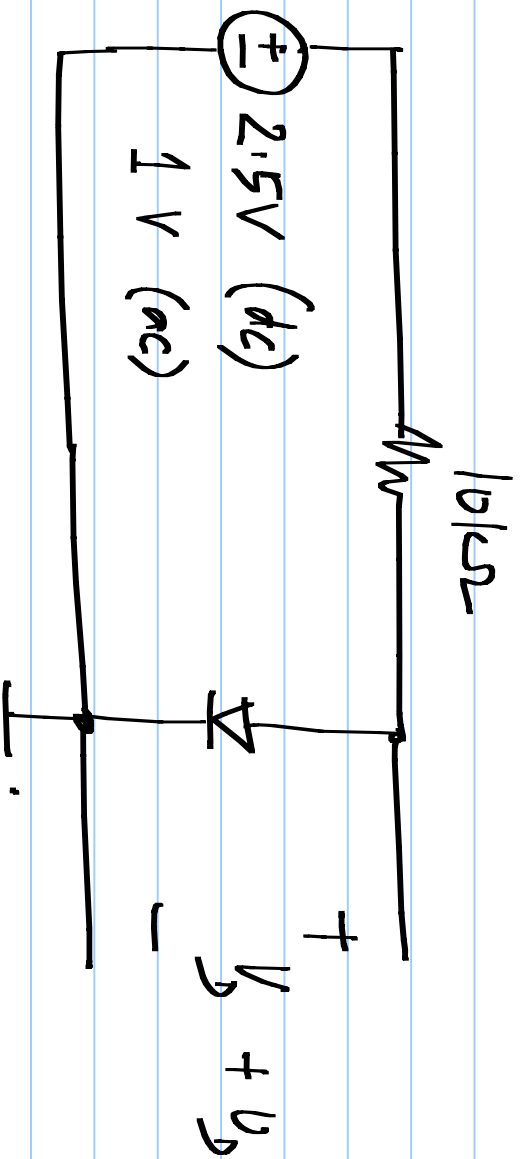
## Small signal incremental analysis (simulation)



Compare  
results to  
hand calculations

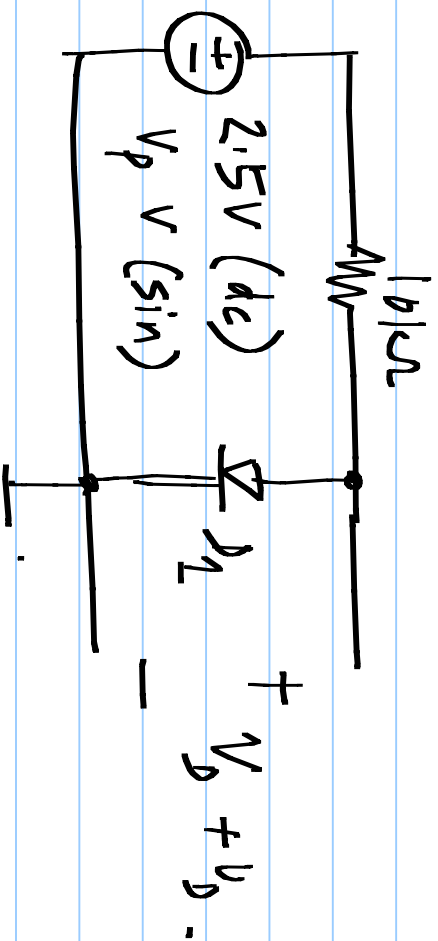
- \* Do .op & .ac analyses & determine  $V_s$  &  $v_s$
- \* Can do .ac over a range of frequencies.
- \* What happens if  $V_p$  (ac magnitude) is changed?

## Small signal incremental analysis (simulation)



- \* Common to use 1V (ac)
- \* The ac part of the output is the "transfer function" from the input to the output

## Large signal analysis with time varying signals



Transient analysis:  
Can't do by hand -  
this is why we use  
a simulator

- \* Use a small  $V_p$  ( $\sim 10mV$ ) and do transient analysis.
- \* Increase the amplitude and see what happens to the output increment.

Basic analyses available in SPICE like simulators:

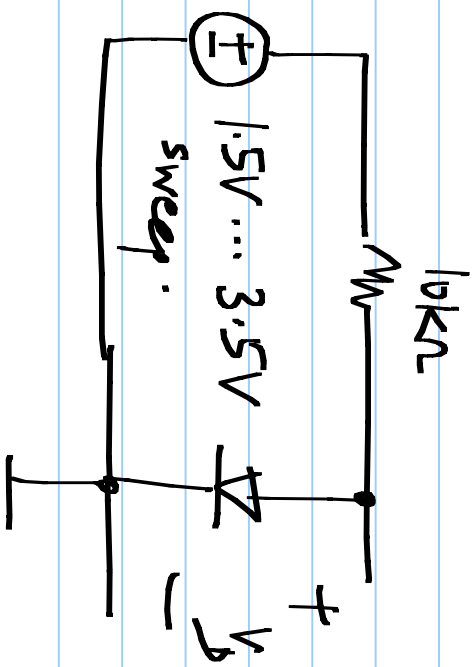
- \* DC analysis - operating point
- \* AC analysis - small signal incremental (linear) analysis over the operating point. Also for transfer functions

\* TRAN (transient) analysis - Full solution to nonlinear differential equations of the circuit.

Can do all of them in a single run

## Other features of a simulator:

\* DC sweep : Do dc operating points at multiple input values. Can be used to determine non linear input-output (dc) relationships.



plot  $V_b$  vs.  $V_{in}$

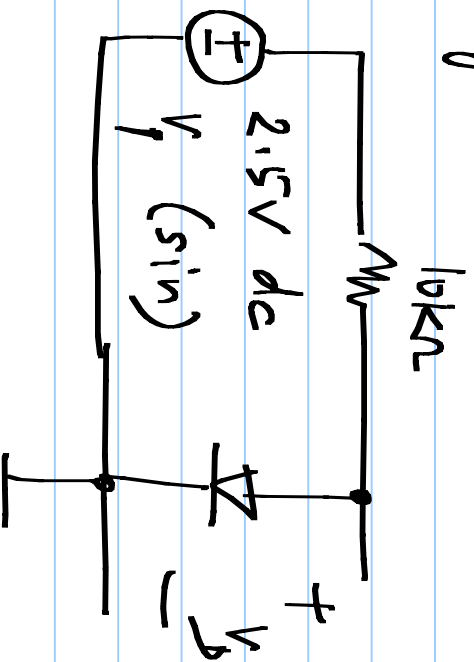
plot  $I_b$  vs.  $V_b$



## Other features of a simulator:

\* Parametric sweep: Can do analyses for different component values.

e.g.:

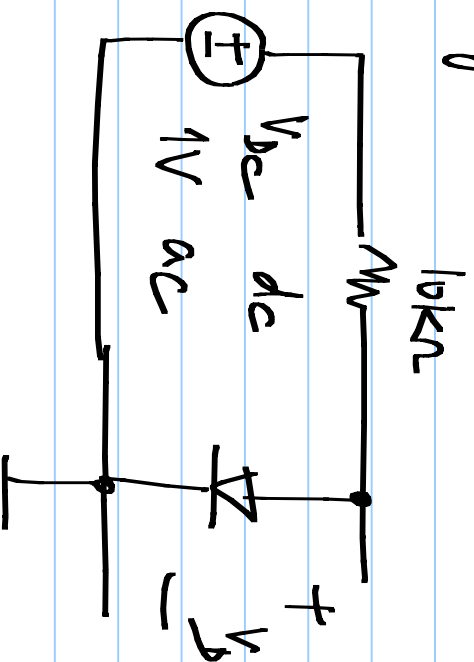


Sweep  $V_p$  from lowV to 1V  
in decade steps & do  
transient analysis

## Other features of a simulator:

\* Parametric sweep: Can do analyses for different component values.

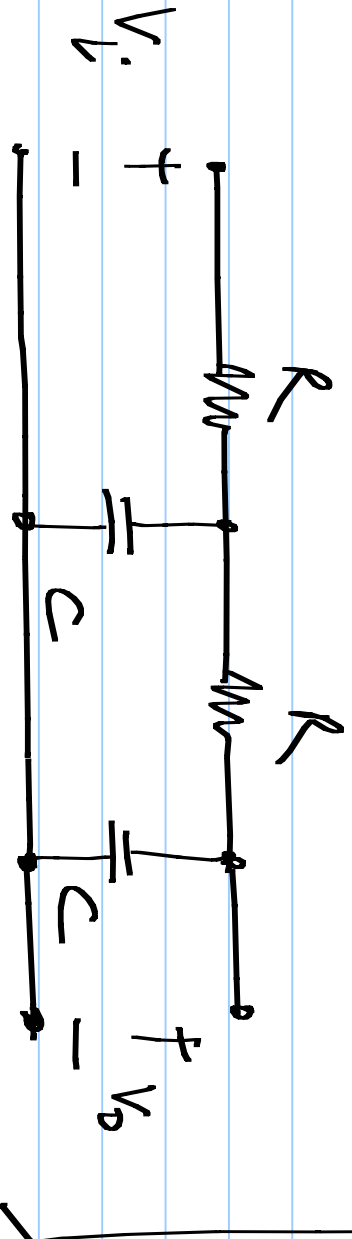
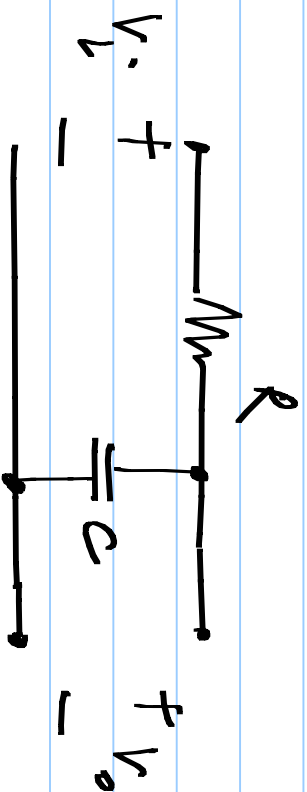
e.g.:



Sweep  $V_{bc}$  from 1V to 3V  
in 1V steps & do  
ac analysis

## Other exercises:

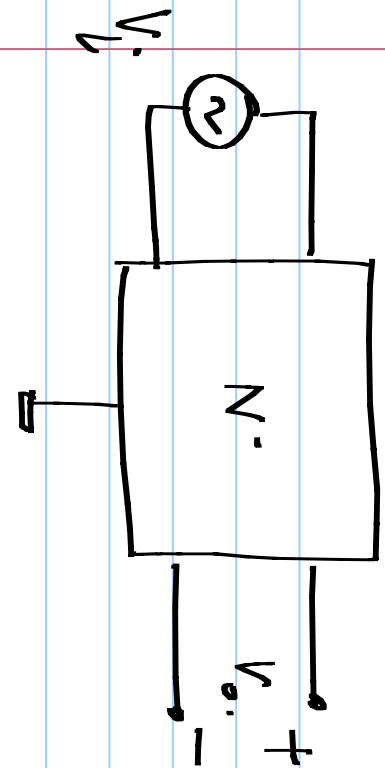
ac analysis for transfer functions:



Plot

$$\left| \frac{V_o}{V_i} \right|, \angle \frac{V_o}{V_i}$$

## Noise simulation:



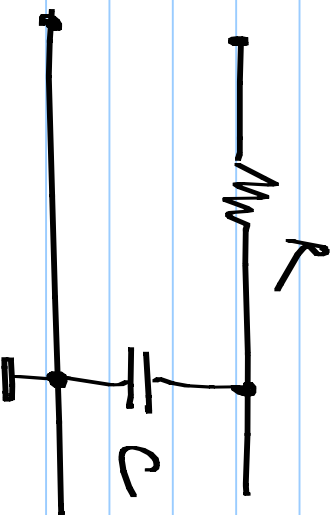
\* Can simulate the output

noise & input referred  
noise spectral densities &  
integrated noise

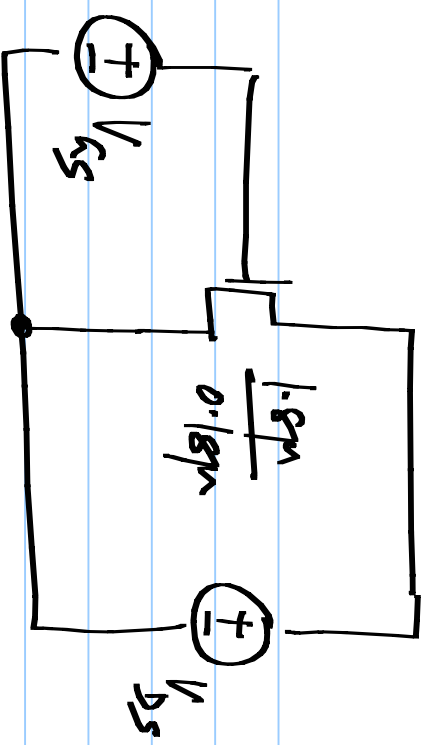
\* Need to specify

- output terminals across which the noise voltage is measured (In most simulators, you can't specify a current. Need to convert using a ccrs)
- input source to which the noise is referred back
- Range of frequencies

## Noise simulation exercises :

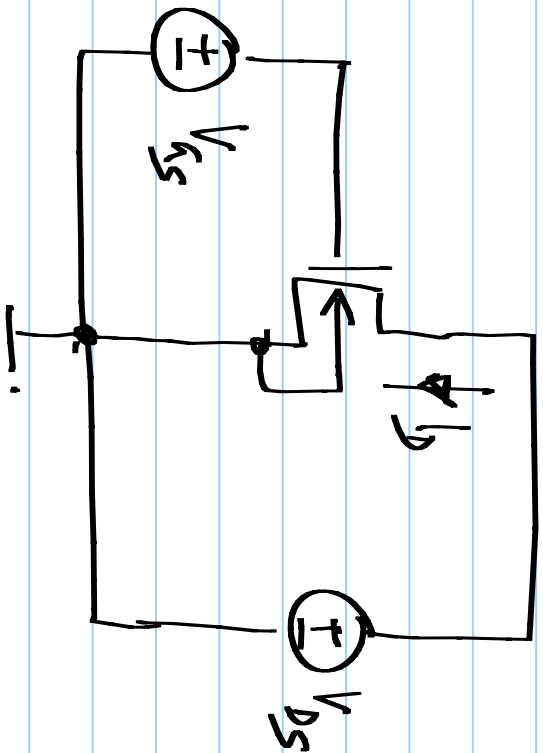


- Verify input referred noise PSD & integrated output noise



- Bias the MOS transistor at  $V_{GS} = 0.7\text{V}$ ,  $V_{DS} = 0.7\text{V}$  & measure  $S_{11}$ . Verify thermal noise PSD & flicker noise corner
- change to  $\frac{3.6\mu\text{m}}{0.36\mu\text{m}}$  etc, & see

## Transistor characteristics:



\* Plot  $I_d$  vs.  $V_{gs}$  for

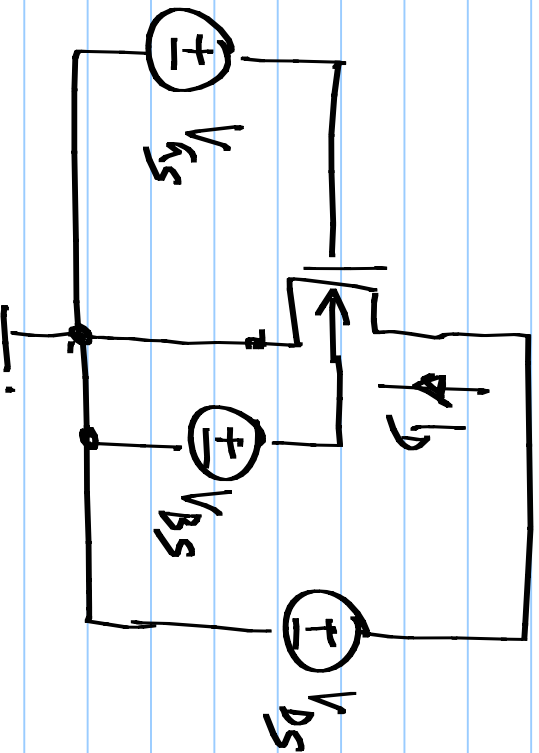
different values of  $V_{ds}$

\*  $T_{eq} \left[ \frac{W}{L} = \frac{1.8\mu m}{0.18\mu m}, \frac{3.6\mu m}{0.36\mu m}, \right.$

$\left. \frac{5.4\mu m}{0.54\mu m}, \frac{7.2\mu m}{0.72\mu m} \right]$

\* Estimate  $\mu C_{ox}$ ,  $V_t$

## Transistor characteristics:



\* Plot  $I_D$  vs.  $V_{GS}$  for

different values of  $V_{DS} (< 0)$

(Fix  $V_{GS}$ )

\* Estimate  $\left(\frac{g_{mbs}}{g_m}\right)$